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U.S. PATENT DOCUMENTS

EXAMINER INITIAL		PATENT NUMBER	ISSUE DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
		6 0 5 1 8 4 9	04/18/00	David, et al.			

FOREIGN PATENT OR PUBLISHED FOREIGN PATENT APPLICATION

		DOCUMENT NUMBER	PUBLIC-ATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUB CLASS	TRANS-LATION YES	TRANS-LATION NO
		0 9 4 2 4 5 9	15.09.99	EP				
	1	0 3 1 2 9 7 1	24.11.98	JP			*	
	1	1 1 2 6 9 4 8	11.05.99	JP			*	

*abstract only

OTHER DOCUMENTS (Including Author, Title, Date, Place of Publication)

MM		Zheleva, et al,. Pendeo-Epitaxy - A New Approach for Lateral Growth of Gallium Nitride Structures, *MRS Internet J. Nitride Semicond. Res. 4S1, G3.38 (1999)*
MM		Thomson, et al., Ranges of Deposition Temperatures Applicable for Metalorganic Vapor Phase Epitaxy of GaN Films Via the Technique of Pendeo-Epitaxy, *MRS Internet J. Nitride Semicond. Res. 4S1, G3.37 (1999)*
MM		T. Gehrke, et al., Pendeo-Epitaxy of Gallium Nitride and Aluminum Nitride Films and Heterostructures on Silicon Carbide Substrate, *MRS Internet J. Semicond. Res. 4S1, G3.2 (1999)*
MM		K. Linthicum, et al., Process Routes for Low Defect-Density GaN on Various Substrates Employing Pendeo-Epitaxial Growth Techniques, *MRS Internet J. Nitride Semicond. Res. 4S1, G4.9 (1999)*
MM		T. Zheleva, et al., Dislocation Density Reduction via Lateral Epitaxy in Selectively Grown GaN Structures, *Appl. Phys. Lett. 71 (17), 27 October 1997, pg. 2472*
MM		K. Linthicum, et al., Pendeoepitaxy of Gallium Nitride Thin Films, *Appl. Phys. Lett. 75 (2), 1999, pg. 196*
MM		T. Zheleva, et al., Pendeo-Epitaxy: A New Approach for Lateral Growth of Gallium Nitride Films, *J. Electronic Materials, 28 (4), 1999, pg. L5*

EXAMINER Matthew Anderson DATE CONSIDERED 7/15/2002

EXAMINER: Initial citation consid r d. Draw lin through citation if not in conformance and not consider d. Include copy of this form with n xt communication to applicant.

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